

SOT-23 Plastic-Encapsulate Transistors

FMMT491 TRANSISTOR (NPN)

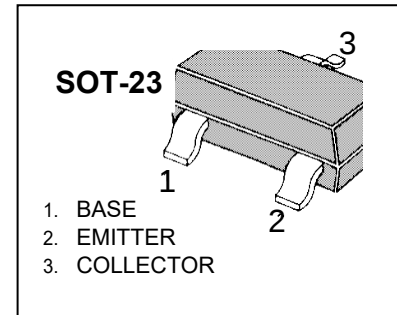
FEATURES

Low equivalent on-resistance

Marking :491

MAXIMUM RATINGS (TA=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current -Continuous	I_C	1000	mA
Collector Power Dissipation	P_C	250	mW
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 to +150	℃

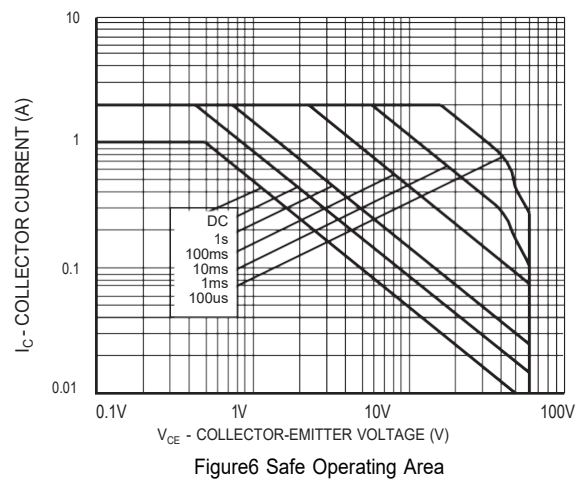
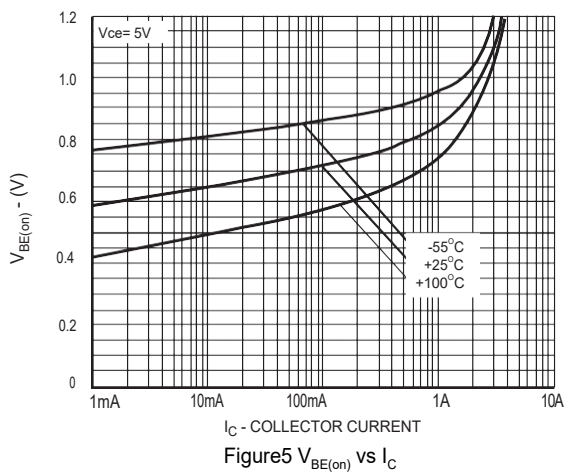
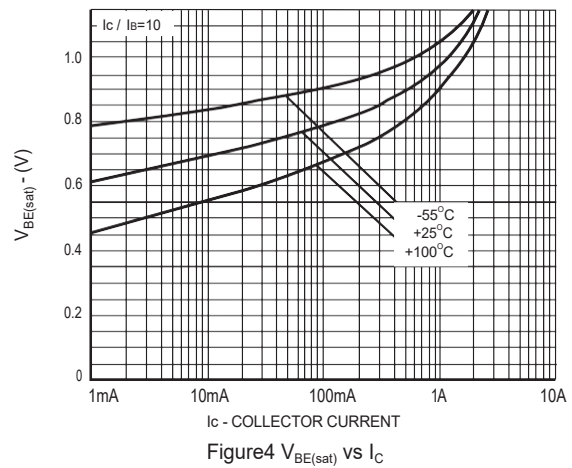
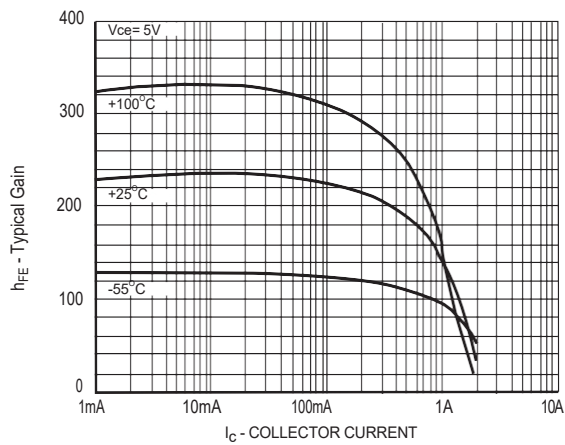
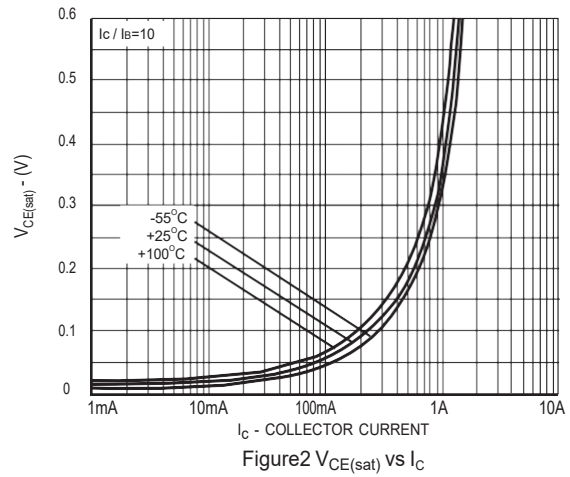
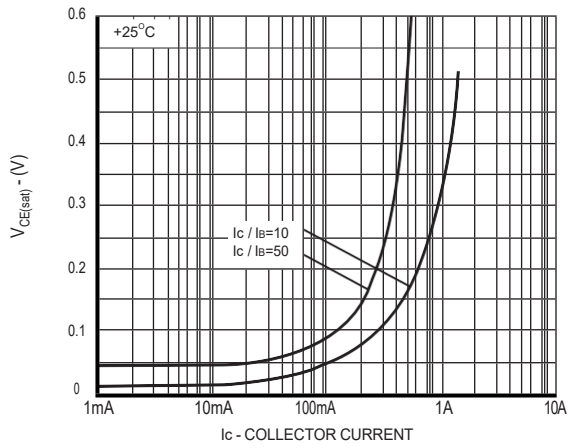


ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=100\mu A, I_E=0$	80			V
Collector-emitter breakdown voltage	V_{CEO}^1	$I_C=10mA, I_B=0$	60			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=5V, I_C=1mA$	100			
	$h_{FE(2)}^1$	$V_{CE}=5V, I_C=500mA$	100		300	
	$h_{FE(3)}^1$	$V_{CE}=5V, I_C=1A$	80			
	$h_{FE(4)}^1$	$V_{CE}=5V, I_C=2A$	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}^1$	$I_C=500mA, I_B=50mA$			0.25	V
	$V_{CE(sat)2}^1$	$I_C=1A, I_B=100mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}^1$	$I_C=1A, I_B=100mA$			1.1	V
Base-emitter voltage	V_{BE}^1	$V_{CE}=5V, I_C=1A$			1	V
Transition frequency	f_T	$V_{CE}=10V, I_C=50mA, f=100MHz$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$			10	pF

¹Measured under pulsed conditions, Pulse width=300 μs , Duty cycle $\leq 2\%$.

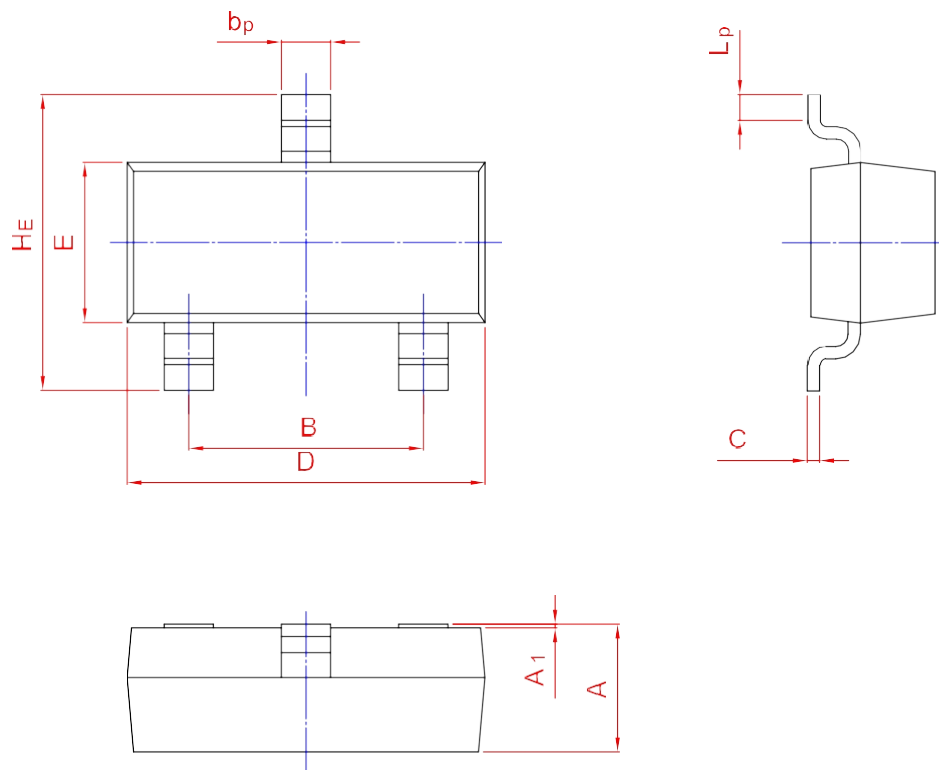
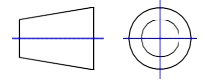
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b _p	C	D	E	H _E	A ₁	L _p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20